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# P-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY						
V <sub>DS</sub> (V)	$R_{DS(on)}$ (m $\Omega$ )(Typ.)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)			
- 40	265 at V <sub>GS</sub> = - 10 V	- 1	1.5 nC			
- 40	380 at V <sub>GS</sub> = - 4.5 V	- 1				

### **FEATURES**

- DT-Trench Power MOSFET
- 100 %  $R_q$  and UIS Tested
- · Lead Free

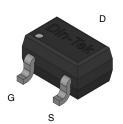
### **APPLICATIONS**

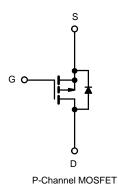
- Power Management
- · PWM Application
- · Load Switch



### **SOT-23 Pin Configuration**

**Top View** 





ABSOLUTE MAXIMUM RATINGS (T <sub>C</sub> = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V <sub>DS</sub>	- 40	V		
Gate-Source Voltage	V <sub>GS</sub>	± 20	]		
Continuous Proin Current /T 4509 C\2	T <sub>C</sub> = 25 °C		- 1	А	
Continuous Drain Current (T <sub>J</sub> = 150° C) <sup>a</sup>	T <sub>C</sub> = 100 °C	I <sub>D</sub>	- 0.65		
Pulsed Drain Current <sup>b</sup>	I <sub>DM</sub>	- 4			
Maximum Power Dissipation <sup>c</sup>	T <sub>C</sub> = 25 °C	P <sub>D</sub>	0.8	W	
waximum rower Dissipation	T <sub>C</sub> = 100 °C		0.32	l vv	
Operating Junction and Storage Temperature Ra	T <sub>J</sub> , T <sub>stg</sub>	- 55 to + 150	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Case (Drain)	R <sub>thJC</sub>	156	°C/W		

#### **Notes**

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R<sub>0JA</sub> is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	$V_{DS}$ $V_{GS} = 0 \text{ V, } I_{D} = -250  \mu\text{A}$		- 40	-	-	V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$		-	- 1.5	V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ -		-	± 100	nA	
Zero Gate Voltage Drain Current	lann	V <sub>DS</sub> = - 40 V, V <sub>GS</sub> = 0 V	ı	-	- 1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	$V_{DS} = -32V$ , $V_{GS} = 0$ V, $T_{J} = 55$ °C	-	-	- 10	μΑ	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 1	-	-	Α	
Drain-Source On-State Resistance <sup>a</sup>	D	V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 1.5 A	-	265	345		
Diani-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = - 4.5 V, I <sub>D</sub> = - 1 A	-	380	500	mΩ	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>		-	91	-	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = -20 \text{ V}, f = 1 \text{ MHz}$	-	11	-		
Reverse Transfer Capacitance	C <sub>rss</sub>		-	9	-		
Total Gate Charge <sup>c</sup>	$Q_g$		-	1.5	-	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	V <sub>DS</sub> = - 15 V, V <sub>GS</sub> = - 10 V, I <sub>D</sub> = - 2 A	-	0.4	-		
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$		-	0.45	-		
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>		-	8.8	-		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD} = -15 \text{ V}, R_g = 3 \Omega,$	-	19	-	ns	
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	I <sub>D</sub> = - 1 A , V <sub>G</sub> s = - 10 V	-	44	-		
Fall Time <sup>c</sup>	t <sub>f</sub>		-	38	-		
Drain-Source Body Diode Ratings and Characteristics <sup>b</sup> (T <sub>C</sub> = 25 °C)							
Continuous Source-Drain Diode Current	I <sub>S</sub>	T <sub>C</sub> = 25 °C	ı	-	- 1	Α	
Pulsed Current	I <sub>SM</sub>		ı	-	- 4	Α	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = - 1 A, V <sub>GS</sub> = 0 V	•	=	-1.2	V	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = -1 A, di/dt = 100 A/μs	ī	13	-	ns	
Reverse Recovery Charge	Q <sub>rr</sub>	1 <sub>F</sub> = -1 A, αι/αι – 100 Α/μ5	-	5.5	-	nC	

#### Notes

- a. Pulse test; pulse width  $\leq$  200  $\mu$ s, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended pe riods may affect device reliability.



TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)

# **Test Circuit**

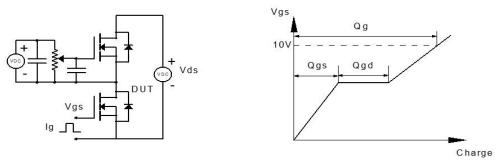


Figure 1: Gate Charge Test Circuit & Waveform

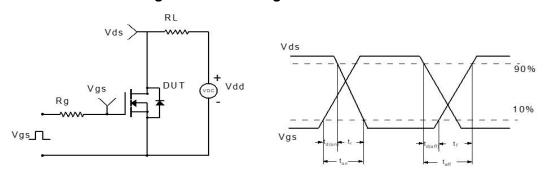


Figure 2: Resistive Switching Test Circuit & Waveform

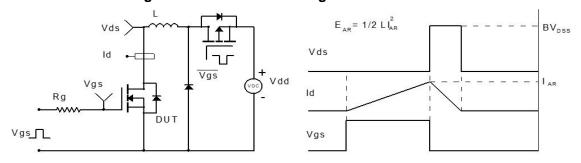


Figure 3: Unclamped Inductive Switching Test Circuit& Waveform

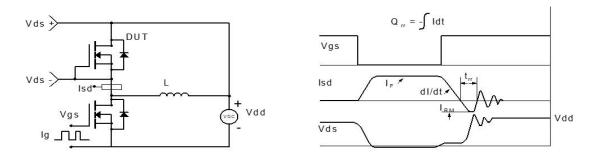
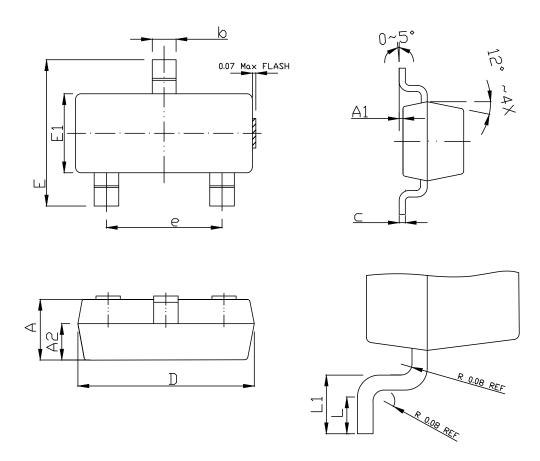


Figure 4: Diode Recovery Test Circuit & Waveform



## SOT-23 PACKAGE OUTLINE



**COMMON DIMENSIONS** (UNITS OF MEASURE=MILLIMETER)

SYMBOL	MILLIMETER			
STIVIDOL	MIN	NOM	MAX	
Α	0.80	1.00	1.30	
A1	0.00	0.05	0.15	
b	0.25	0.40	0.55	
С	0.11 BSC			
D	2.60	2.90	3.20	
E	2.10	2.40	2.70	
E1	1.10	1.30	1.48	
е	1.90 BSC			
L	0.17	-		
L1	0.28	0.40	0.53	
A2	0.60 REF			





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